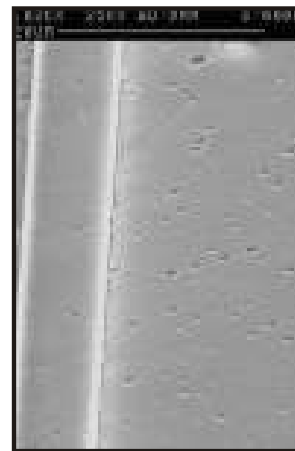
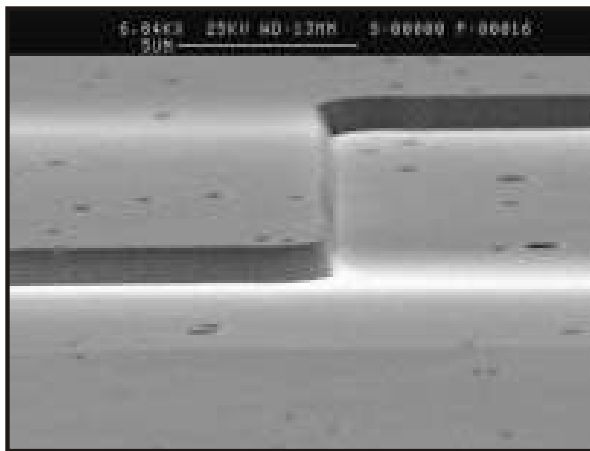


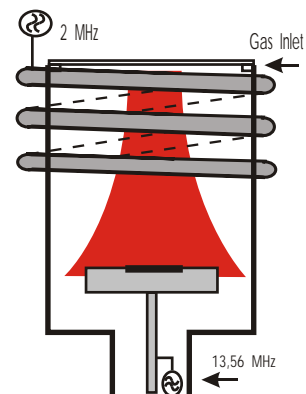
Plasmalab Data

InGaN / GaN ICP Etching



OPT application lab:
anisotropic InGaN/ GaN etches

Plasmalab 80 Plus
Plasmalab System 100
Plasmalab System 133



Technology:

Inductive Coupled Plasma ICP-RIE
13 MHz induced RF bias
Cl₂ based process

Results:

rate : 0.1 - 1 $\mu\text{m}/\text{min}$
selectivity to SiO₂ mask > 5 : 1
selectivity to Ni mask > 20 : 1
good uniformity: +/- 2.5 % (2")
anisotropic profile
smooth etched sidewalls